TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type ( $\pi$ -MOSVI)

# 2SK4012

#### **Switching Regulator Applications**

Low drain-source ON-resistance : R<sub>DS</sub> (ON) = 0.33 Ω (typ.)

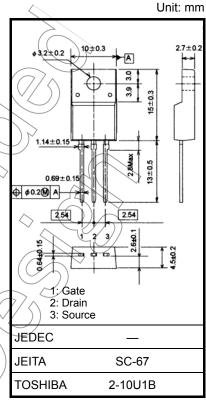
• High forward transfer admittance :  $|Y_{fs}| = 8.5 \text{ S (typ.)}$ 

Low leakage current :  $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 500 \text{ V)}$ 

• Enhancement mode :  $V_{th} = 2.0 \text{ to } 4.0 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$ 

### Absolute Maximum Ratings (Ta = 25°C)

Characteri	stic	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	$(\mathcal{N} \land)$
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	500	(V)
Gate-source voltage		$V_{GSS}$	±30	V
Drain current	DC (Note 1)	ΙD	13	A
	Pulse (Note 1)	I <sub>DP</sub>	52	Α
Drain power dissipation	(Tc = 25°C)	P <sub>D</sub>	45	W
Single-pulse avalanche	e energy (Note 2)	EAS	1170	mJ
Avalanche current		IAR	13	A
Repetitive avalanche e	nergy (Note 3)	EAR	)) 4.5	mJ
Channel temperature		Tch	150	∕ °C
Storage temperature ra	inge	T <sub>stg</sub>	-55 to 150	<i>J</i> ,c



Weight: 1.7 (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

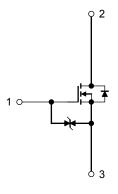
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	Rth (ch-c)	2.78	°C / W
Thermal resistance, channel to ambient	Rth (ch-a)	62.5	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 11.8 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 13 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



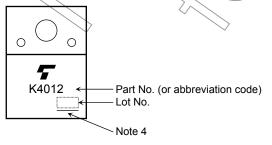
### **Electrical Characteristics (Ta = 25°C)**

Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source br	eakdown voltage	V (BR) GSS	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	_	_	V
Drain cutoff curr	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V		_	100	μΑ
Drain-source b	reakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	500	_	_	V
Gate threshold	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	) / _	4.0	V
Drain-source O	N-resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A	<u> </u>	0.33	0.4	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.5 A	4.0	8.5	_	S
Input capacitance		C <sub>iss</sub>		_	2400	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	18	_	pF
Output capacitance		Coss		_	220		
Switching time	Rise time	t <sub>r</sub>	10 V I <sub>D</sub> = 6.5 A V <sub>OUT</sub> V <sub>GS</sub>	- (	25	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
	Turn-on time	t <sub>on</sub>	0 V — R <sub>L</sub> = 31 Ω		70	) –	- ns
	Fall time	t <sub>f</sub>	V <sub>DD</sub> ≈ 200 V	7(5)	10	_	
	Turn-off time	t <sub>off</sub>	Duty ≤ 1%, t <sub>w</sub> = 10 μs	)	95	_	
Total gate charg		Qg		_	50	_	
Gate-source ch	arge	Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$	_	30	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>		_	20	_	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	IÓR		_	_	13	Α
Pulse drain reverse current (Note 1)	) I <sub>DRP</sub>	_	-	_	52	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V	_	1000	_	ns
Reverse recovery charge	Qrr	dl <sub>DR</sub> / dt = 100 Å / μs	_	11	_	μC

## Marking

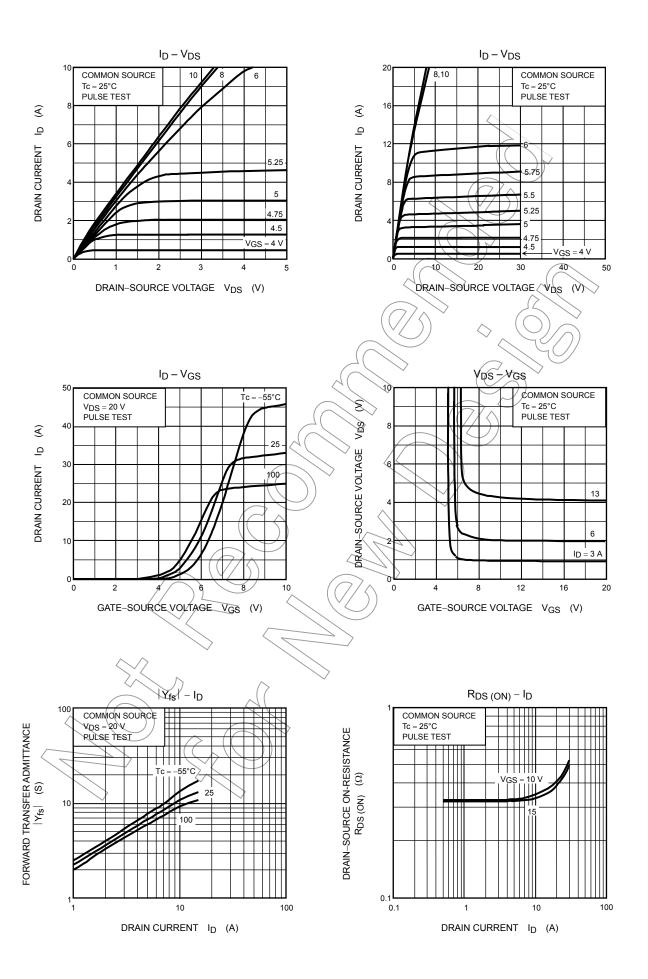


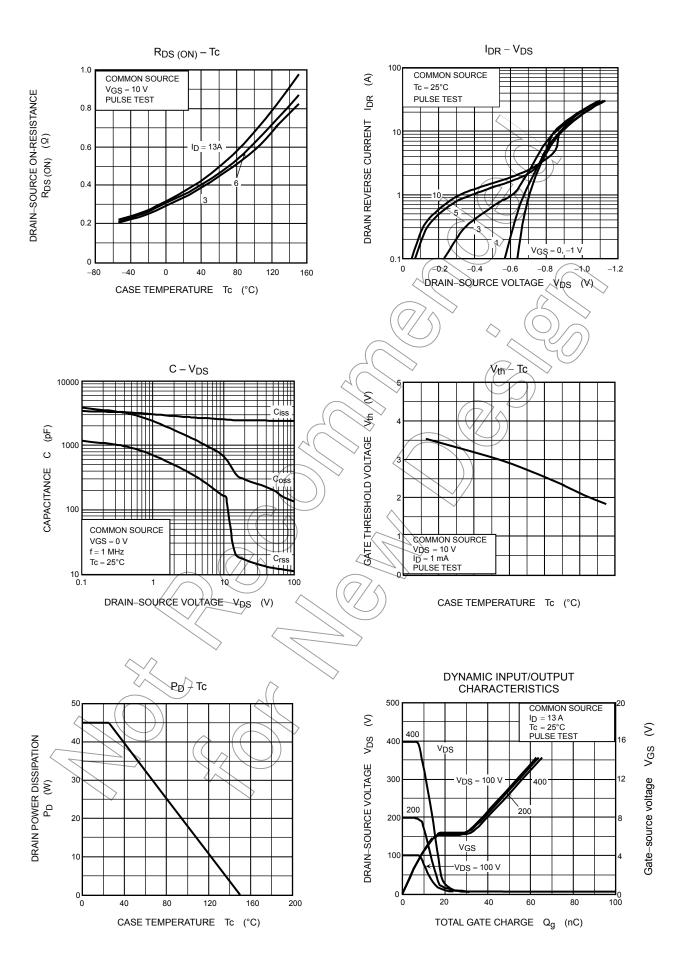
Note 4: A line under a Lot No. identifies the indication of product Labels.

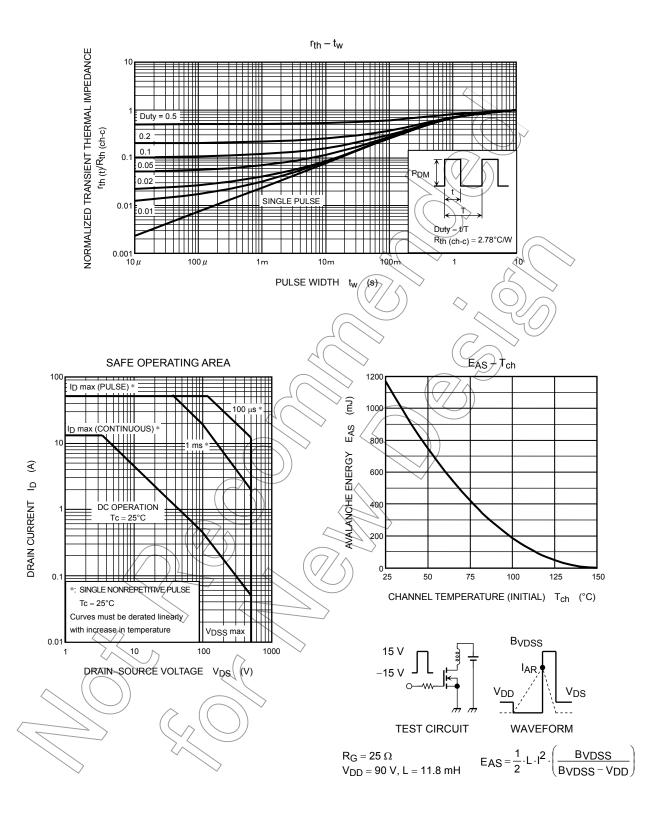
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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